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ABSTRACT

DOUBLE POLYSILICON BIPOLAR TRANSISTOR AND METHOD OF MANUFACTURE THEREFOR

A bipolar transistor, and manufacturing method therefor, with a substrate having a collector region and a base structure provided thereon. An emitter structure is formed over the base structure and an extrinsic base structure is formed over the base structure and over the collector region beside and spaced from the emitter structure. A dielectric layer is deposited over the substrate and connections are formed to the extrinsic base structure, the emitter structure and the collector region.

FIGURE 9



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